| Name: <br> Enrolment No: |  |  |  |
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| UNIVERSITY OF PETROLEUM AND ENERGY STUDIES <br> End Semester Examination, December 2018 <br> Coursee: Basic Electronics Engineering (PHYS-1003) <br> Semester: I <br> Programme: B.Tech (CIT: IOT, Big Data, DevOps, CSF, Cyber Law/IPR, OGI, OSS, Ai\&ML) <br> Time: 03 hrs. <br> Max. Marks: 100 <br> Instructions: <br> 1. Draw suitable circuit diagrams wherever required to justify your answer. <br> 2. Your answer should be concise and to the point. |  |  |  |
| SECTION A(All questions are compulsory.) |  |  |  |
| 1. | Describe the difference between donor and acceptor impurities. | [4] | CO1 |
| 2. | Discuss with the help of a circuit diagram, how a zener diode can be used as a voltage regulator. | [4] | CO1 |
| 3. | A center-tapped full wave rectifier has the load resistance $R_{L}=2000 \mathrm{ohm}$. The forward resistance $\mathrm{R}_{\mathrm{F}}$ of each diode is 20 ohm . The voltage across half of the secondary winding is given by the equation $\mathrm{V}=400 \sin 14 t$. Calculate the Maximum current, Direct current and ripple factor. | [4] | CO1 |
| 4. | Determine the current gain, $\alpha_{\mathrm{dc}}$ if emitter current, $I_{E}=2.8 \mathrm{~mA}$ and base current, $I_{B}=20$ $\mu \mathrm{A}$. | [4] | CO2 |
| 5. | An amplifier operating over the frequency range from 10 to 18 MHz has a $8 \mathrm{k} \Omega$ input resistor. What is the rms noise voltage at the input to this amplifier if the ambient temperature is $27^{\circ} \mathrm{C}$ ? (Boltzmann constant, $\mathrm{k}=1.38 \times 10^{-23} \mathrm{~J} / \mathrm{K}$ ) | [4] | CO4 |
| SECTION B <br> (All questions are compulsory. Question no. 7 has internal choice.) |  |  |  |
| 6. | (a) Using diode equation, determine the diode current at $20^{\circ} \mathrm{C}$ for a silicon diode with $\mathrm{I}_{\mathrm{s}}=$ 50 nA and an applied forward bias of 0.6 V . <br> (b) Calculate the value of thermal voltage at room temperature. (Boltzmann constant, $\mathrm{k}=$ $1.38 \times 10^{-23} \mathrm{~J} / \mathrm{K}$ ) | [ $5+5]$ | CO1 |
| 7. | Discuss the construction and working of common base transistor amplifier, write the expression for current gain and emitter current. Also draw the input and output characteristics. <br> OR <br> Explain the construction and working of depletion mode of depletion type MOSFET with the help of a suitable diagram. | [10] | CO 2 |
| 8. | How the Amplifiers can be classified based on the operating point? Which types of | [8+2] | CO3 |


13.

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| SECTION A <br> (All questions are compulsory.) |  |  |  |
| 1. | What do you understand by the terms 'drift' and 'diffusion' for a semiconductor? Write the expression for total current density. | [4] | CO1 |
| 2. | Write the steps in determining the output waveform from an unbiased clamper. | [4] | CO1 |
| 3. | For the series diode configuration of given circuit determine $V_{D}, V_{R}$, and $I_{D}$. | [4] | CO1 |
| 4. | If Current gain $\beta_{\mathrm{dc}}=180$ and collector current $I_{C}=2.0 \mathrm{~mA}$, find Emitter current and base current. | [4] | CO 2 |
| 5. | Calculate the noise voltage at the input of a television RF Amplifier using a device that has a 200 ohm equivalent noise resistance and 100 Ohm input resistor. The bandwidth of the amplifier is 4 MHz and the temperature is $15^{\circ} \mathrm{C}$. (Boltzmann constant, $\mathrm{k}=1.38$ $\mathrm{x} 10^{-23} \mathrm{~J} / \mathrm{K}$ ) | [4] | CO 4 |
| SECTION B <br> (All questions are compulsory. Question no. 7 has internal choice.) |  |  |  |
| 6. | (a) Discuss the effect of biasing on the width of depletion layer of PN junction diode. <br> (b) A sample of intrinsic silicon has 0.13 and $0.05 \mathrm{~m}^{2} / \mathrm{V}-\mathrm{s}$ electron and hole mobilities respectively at 300 K . If the density of electrons and holes are each equal to $1.5 \times 10^{16}$ $\mathrm{m}^{-3}$ at 300 K , find the electrical conductivity for addition of 1 donor impurity atom in $10^{9}$ silicon atoms. | $[5+5]$ | CO1 |
| 7. | Draw the output characteristics of a common emitter transistor configuration. Describe a load line and discuss the significance of an operating point. <br> OR | [10] | CO 2 |


|  | Explain the construction and working of enhancement mode of depletion type MOSFET with the help of a suitable diagram. |  |  |
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| 8. | Write the characteristics of an ideal operational Amplifier. Draw the circuit diagram of op-amp as summer and find out the expression for the output voltage. | [10] | CO3 |
| 9. | Explain the importance of modulation and demodulation in communication system with their definitions and discuss different types of modulation along with diagram. | [10] | CO 4 |
| SECTION C(Q10 and Q11 are compulsory. Attempt any set of Q12 \& 13.) |  |  |  |
| 10. | Discuss the Amplitude Modulation superhetrodyne receiver by explaining the function of each stage with the help of a suitable block diagram. | [10] | CO4 |
| 11. | Explain the advantage of negative feedback over positive feedback and derive the relation for overall voltage gain of amplifier with negative feedback. | [10] | CO3 |
| 12. | Sketch the output waveform from the following clamper network for the given input signal: | [10] | CO1 |
| 13. | Find the output voltage for an input voltage of $80 \mu \mathrm{~V}$ for the given circuit The resistor values are $\mathrm{R}_{\mathrm{f}}=470 \mathrm{k} \Omega, \mathrm{R}_{1}=4.3 \mathrm{~K} \Omega, \mathrm{R}_{2}=33 \mathrm{~K} \Omega$ and $\mathrm{R}_{3}=33 \mathrm{~K} \Omega$ | [10] | $\mathrm{CO} 3$ |
| 12. | Determine the range of Vi that will maintain $\mathrm{V}_{\mathrm{L}}$ at 8 V and not exceed the maximum power rating of Zener diode. | [10] | CO1 |



